

Patent Abstracts of Japan

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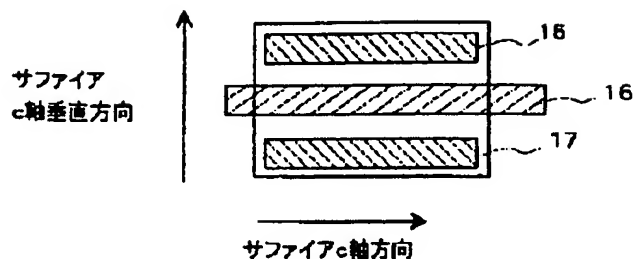
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APPLICANT : NEC CORP;

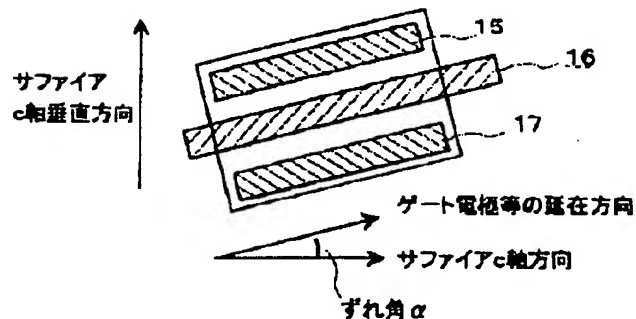
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INT.CL. : H01L 29/778 H01L 21/338 H01L 29/812
H01L 21/205 H01L 29/201

TITLE : SEMICONDUCTOR DEVICE



(a)



(b)

ABSTRACT : PROBLEM TO BE SOLVED: To improve productivity, a heat radiating characteristic and the high speed operability of an element in a group III nitride semiconductor element.

SOLUTION: An epitaxial growing layer constituted of a group III nitride semiconductor is formed on a sapphire substrate with a face A ((11-20) face) as a main face. Then, a gate electrode 16, a source electrode 15 and a drain electrode 17 are formed on it. The extending directions of the electrodes are arranged to become the angle of within 20° with respect to a sapphire c-axis.

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